
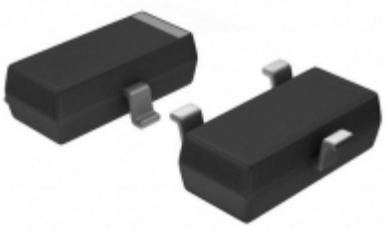

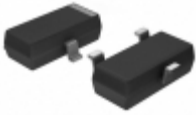





	<p>SI2365EDS-T1-GE3</p>
	<p>Hersteller-Teilenummer: SI2365EDS-T1-GE3</p> <p>Hersteller / Marke: Vishay / Siliconix</p> <p>Teil der Beschreibung: MOSFET P-CH 20V 5.9A TO-236</p> <p>Datenblätter:  SI2365EDS-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 167558 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
	
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI2365EDS-T1-GE3
Hersteller	Vishay / Siliconix
Beschreibung	MOSFET P-CH 20V 5.9A TO-236
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	167558 pcs Stock
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-236-3, SC-59, SOT-23-3
Supplier Device-Gehäuse	TO-236
Verlustleistung (max)	1W (Ta), 1.7W (Tc)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 °C	5.9A (Tc)
Rds On (Max) @ Id, Vgs	32 mOhm @ 4A, 4.5V
VGS (th) (Max) @ Id	1V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	36nC @ 8V
Eingabekapazität (Ciss) (Max) @ Vds	-
Antriebsspannung (Max Rds On, Min Rds On)	1.8V, 4.5V
Vgs (Max)	±8V
Verpackung	Tape & Reel (TR)

SI2365EDS-T1-GE3 ist neu im Original, Suche SI2365EDS-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI2365EDS-T1-GE3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI2365EDS-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI2365EDS-M Original</p>	 <p>SI2356DS-T1-GE3 Vishay / Siliconix MOSFET N-CH 40V 4.3A SOT-23</p>	 <p>SI2366DS-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 30V 5.8A SOT-23</p>	 <p>SI2365EDS-T1-E3 Son SI2365EDS-T1-E3 Son</p>
 <p>SI2365EDS VISHAY SI2365EDS VISHAY</p>	 <p>SI2356DS-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 40V 4.3A SOT-23</p>	 <p>SI2365EDS-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 20V 5.9A TO-236</p>	 <p>SI2366DS-T1-E3 VISHAY SI2366DS-T1-E3 VISHAY</p>

heiße Teile

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|--|---|--|---|--|
|  SI2341DS-T1-GE3 |  SI2341DS-T1-GE3 |  SI2342DS-T1-E3 |  SI2342DS-T1-GE3 |  SI2342DS-T1-GE3 |
|  SI2343ADS-T1-GE3 |  SI2343CDS |  SI2343CDS-T1-E3 |  SI2343CDS-T1-GE3 |  SI2343CDS-T1-GE3 |
|  SI2343DS-T1-E3 |  SI2343DS-T1-E3 |  SI2343DS-T1-GE3 |  SI2343DS-T1-GE3 |  SI2344DS-E3 |
|  SI2347DS-T1-GE3 |  SI2347DS-T1-GE3 |  SI2351DS-T1-E3 |  SI2351DS-T1-E3 |  SI2351DS-T1-GE3 |
|  SI2351DS-T1-GE3 |  SI2356DS-T1-GE3 |  SI2356DS-T1-GE3 |  SI2356EDS |  SI2365EDS-T1-GE3 |
|  SI2366DS-T1-E3 |  SI2366DS-T1-GE |  SI2366DS-T1-GE3 |  SI2366DS-T1-GE3 |  SI2367DS-T1-E3 |
|  SI2367DS-T1-GE3 |  SI2367DS-T1-GE3 |  SI2369DS-T1-GE3 |  SI2369DS-T1-GE3 |  SI2371EDS-T1-GE3 |
|  SI2371EDS-T1-GE3 |  SI2372DS-T1-E3 |  SI2372DS-T1-GE3 |  SI2372DS-T1-GE3 |  SI2374DS-T1-GE3 |
|  SI2374DS-T1-GE3 |  SI2377DS-T1-GE3 |  SI2377EDS |  SI2377EDS-T1-E3 |  SI2377EDS-T1-GE3 |
|  SI2377EDS-T1-GE3 |  SI2392ADS-T1-E3 |  SI2392ADS-T1-GE3 |  SI2392ADS-T1-GE3 |  SI2392DS-T1-GE3 |

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